



NTE369 Silicon NPN Transistor TV Vertical Deflection, Switch

Description:

The NTE369 is an NPN transistor in a TO66 type case designed for high voltage inverters, converters, regulators, and switching circuits.

Features:

- High Voltage: $V_{CBO} = 800V$
- Gain Specified to 200mA

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Emitter Voltage, V_{CEO}	400V
Collector–Base Voltage, V_{CBO}	800V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	1A
Base Current, I_B	300mA
Total Device Dissipation, P_D	40W
Operating Junction Temperature, T_J	$+150^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ C$
Thermal Resistance, Junction–to–Case, R_{thJC}	$3.12^\circ C/W$

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	400	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V$	–	–	100	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$	–	–	100	mA
ON Characteristics						
DC Current Gain	h_{FE}	$I_C = 200mA, V_{CE} = 10V$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$	–	–	5	V
Dynamic Characteristics						
Current Gain–Bandwidth Product	f_T	$I_E = -100mA, V_{CE} = 10V, f = 1MHz$	–	7	–	MHz

